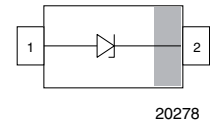
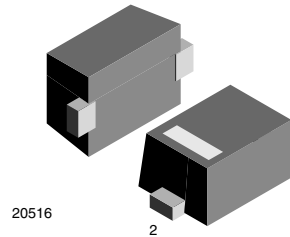


ESD-Protection Diode in SOD923

Features

- Single-line ESD-protection device
- ESD-immunity acc. IEC 61000-4-2
 - > 20 kV contact discharge
 - > 30 kV air discharge
- Tiny SOD923 package
- Package height = 0.4 mm
- Typ. capacitance 12 pF ($V_R = 2.5\text{ V}$; $f = 1\text{ MHz}$)
- Leakage current $< 0.1\ \mu\text{A}$ ($V_R = 5\text{ V}$)
- Lead (Pb)-free component
- Nonmagnetic package material
- "Green" molding compound
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



Marking (example only)



bar = Cathode marking
 X = Date code
 Y = Type code (see table below)

Ordering Information

Device name	Ordering code	Taped units per reel (8 mm tape on 7" reel)	Minimum order quantity
VESD05A1B-02Z	VESD05A1B-02Z-GS08	8000	8000

Package Data

Device name	Package name	Type code	Weight	Molding compound flammability rating	Moisture sensitivity level	Soldering conditions
VESD05A1B-02Z	SOD923	H	0.45 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals

Absolute Maximum Ratings

Rating	Test condition	Symbol	Value	Unit
Peak pulse current	acc. IEC 61000-4-5, $t_p = 8/20\ \mu\text{s}/\text{single shot}$	I_{PPM}	3	A
Peak pulse power	acc. IEC 61000-4-5, $t_p = 8/20\ \mu\text{s}/\text{single shot}$	P_{PP}	33	W
ESD immunity	contact discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 20	kV
	air discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 30	kV
Operating temperature	junction temperature	T_J	- 40 to + 125	°C
Storage temperature		T_{STG}	- 55 to + 150	°C

BiAs-Mode (Bidirectional Asymmetrical protection mode)

With the **VESD05A1B-02Z** one signal- or data-lines (L1) can be protected against voltage transients. With pin 1 connected to ground and pin 2 connected to a signal- or data-line which has to be protected. As long as the voltage level on the data- or signal-line is between 0 V (ground level) and the specified **Maximum Reverse Working Voltage** (V_{RWM}) the protection diode between data line and ground offers a high isolation to the ground line. The protection device behaves like an open switch.

As soon as any positive transient voltage signal exceeds the break through voltage level of the protection diode, the diode becomes conductive and shorts the transient current to ground. Now the protection device behaves like a closed switch. The **Clamping Voltage** (V_C) is defined by the **Breakthrough Voltage** (V_{BR}) level plus the voltage drop at the series impedance (resistance and inductance) of the protection device.

Any negative transient signal will be clamped accordingly. The negative transient current is flowing in the forward direction of the protection diode. The low **Forward Voltage** (V_F) clamps the negative transient close to the ground level.

Due to the different clamping levels in forward and reverse direction the **VESD05A1B-02Z** clamping behaviour is **Bidirectional** and **Asymmetrical (BiAs)**.



20280

Electrical Characteristics

Ratings at 25 °C ambient temperature, unless otherwise specified

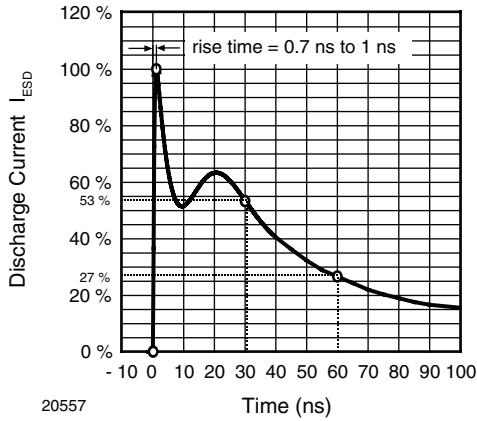
VESD05A1B-02Z

BiAs mode (between pin 1 and pin 2)

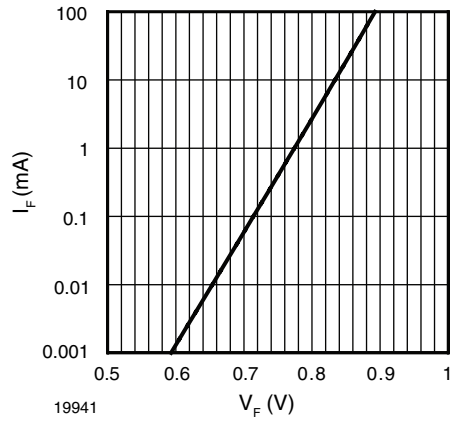
Parameter	Test conditions/remarks	Symbol	Min.	Typ.	Max.	Unit
Protection paths	number of lines which can be protected	N_{lines}			1	lines
Reverse stand off voltage	at $I_R = 0.1 \mu A$	V_{RWM}	5			V
Reverse current	at $V_R = 5 V$	I_R		0.01	0.1	μA
Reverse break down voltage	at $I_R = 1 mA$	V_{BR}	6	6.8	7.5	V
Reverse clamping voltage	at $I_{PP} = 1 A$	V_C		8	9.5	V
	at $I_{PP} = I_{PPM} = 3 A$	V_C		8.9	11	V
Forward clamping voltage	at $I_{PP} = 0.2 A$	V_F		0.95	1.2	V
	at $I_{PP} = 1 A$	V_F		1.3		V
	at $I_{PP} = I_{PPM} = 3 A$	V_F		1.9		V
Capacitance	at $V_R = 0 V$; $f = 1 MHz$	C_D		19	23	pF
	at $V_R = 2.5 V$; $f = 1 MHz$	C_D		12		pF

Typical Characteristics

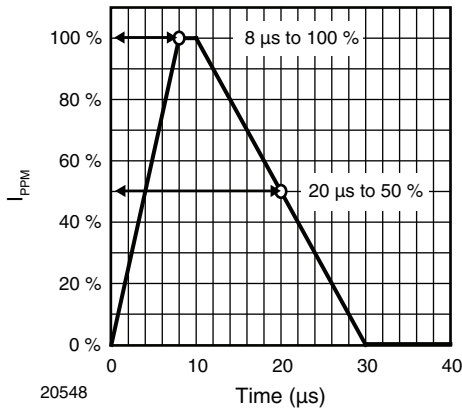
$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified



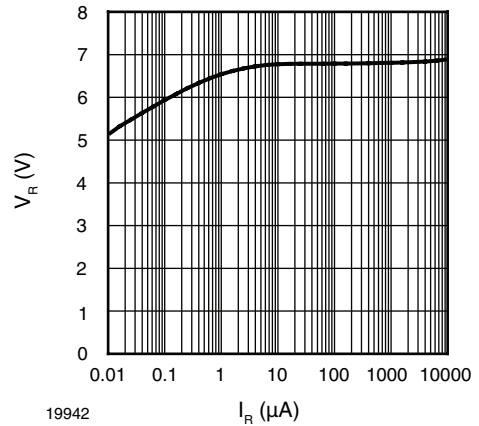
20557
Figure 1. ESD Discharge Current Wave Form acc. IEC 61000-4-2 (330 Ω /150 pF)



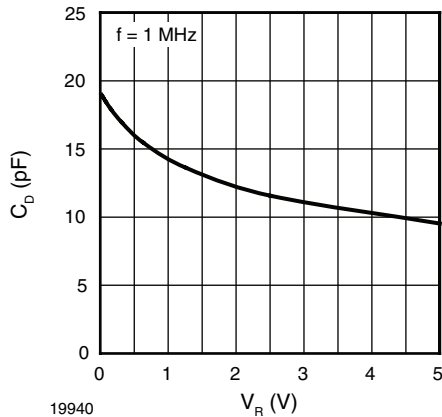
19941
Figure 4. Typical Forward Current I_F vs. Forward Voltage V_F



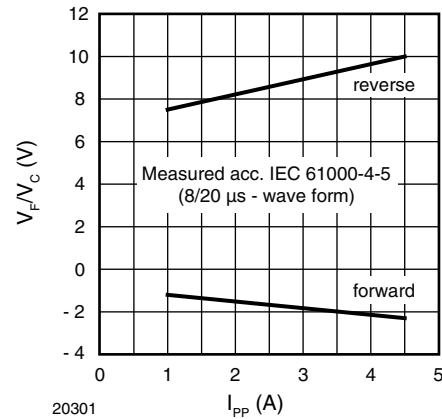
20548
Figure 2. 8/20 μs Peak Pulse Current Wave Form acc. IEC 61000-4-5



19942
Figure 5. Typical Reverse Voltage V_R vs. Reverse Current I_R



19940
Figure 3. Typical Capacitance C_D vs. Reverse Voltage V_R



20301
Figure 6. Typical Clamping Voltage vs. Peak Pulse Current I_{PP}

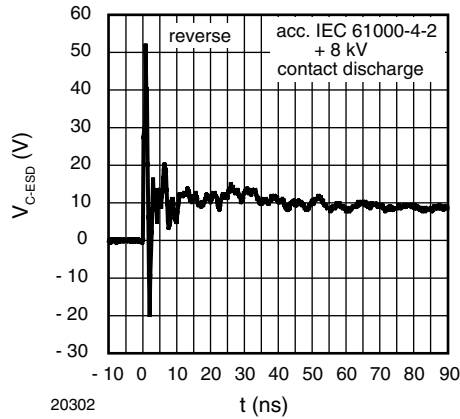


Figure 7. Typical Clamping Performance at + 8 kV Contact Discharge (acc. IEC 61000-4-2)

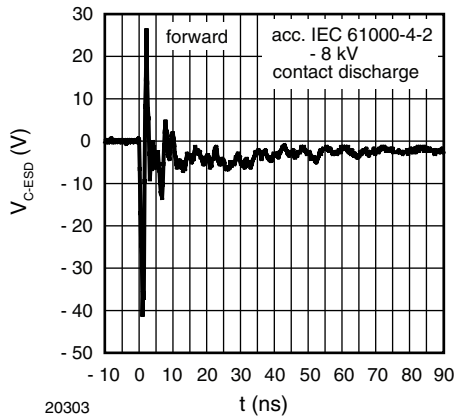


Figure 8. Typical Clamping Performance at - 8 kV Contact Discharge (acc. IEC 61000-4-2)

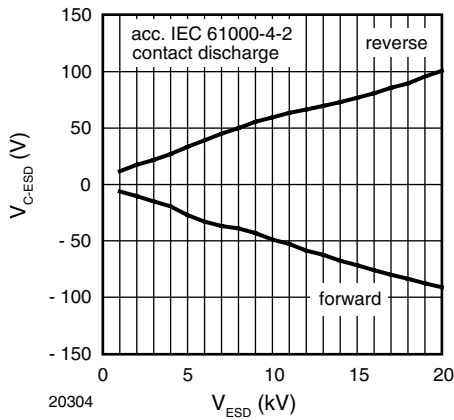
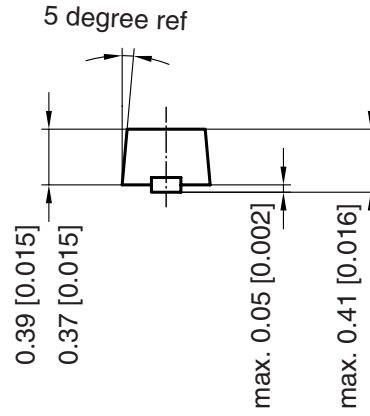
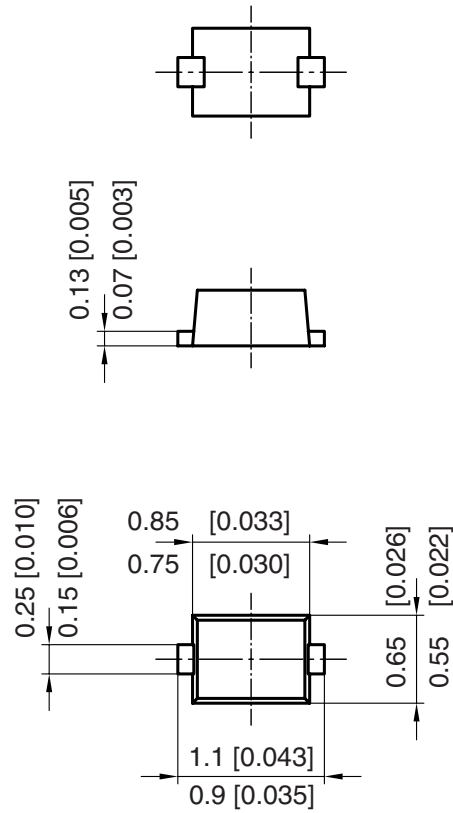
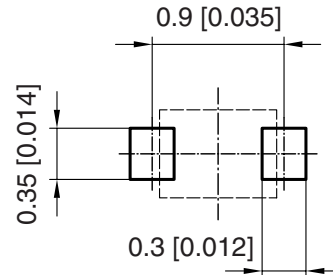


Figure 9. Typical Clamping Voltage at ± ESD Contact Discharge (acc. IEC 61000-4-2)

Package Dimensions in millimeters (inches): **SOD923**



foot print recommendation:



Document no.: S8-V-3880.05-001 (4)

Rev. 1 - Date: 05.July.2006

20096

Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA.
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design
and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany



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